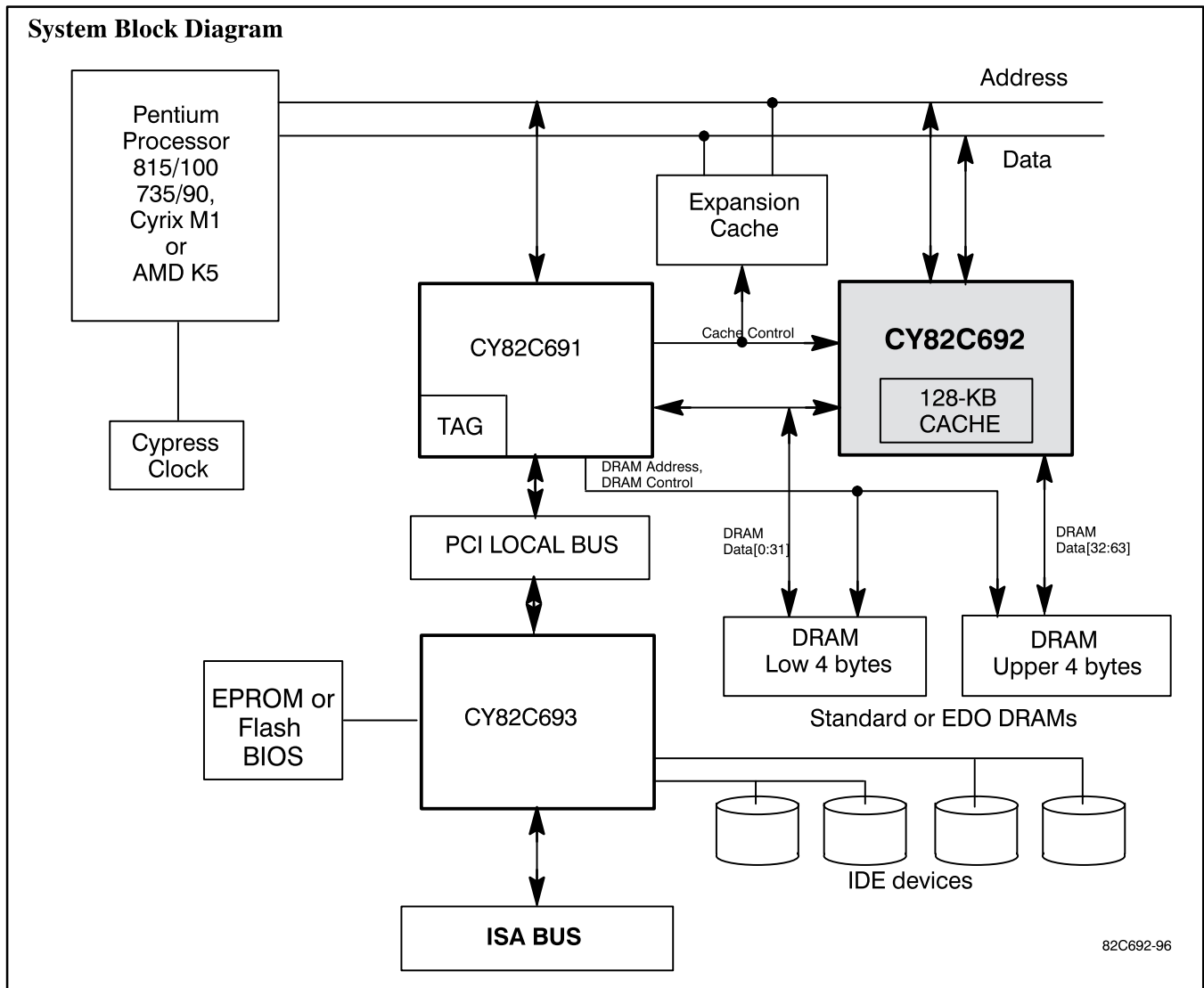




Pentium™ hyperCache™ Chipset Data-Path/Integrated Cache

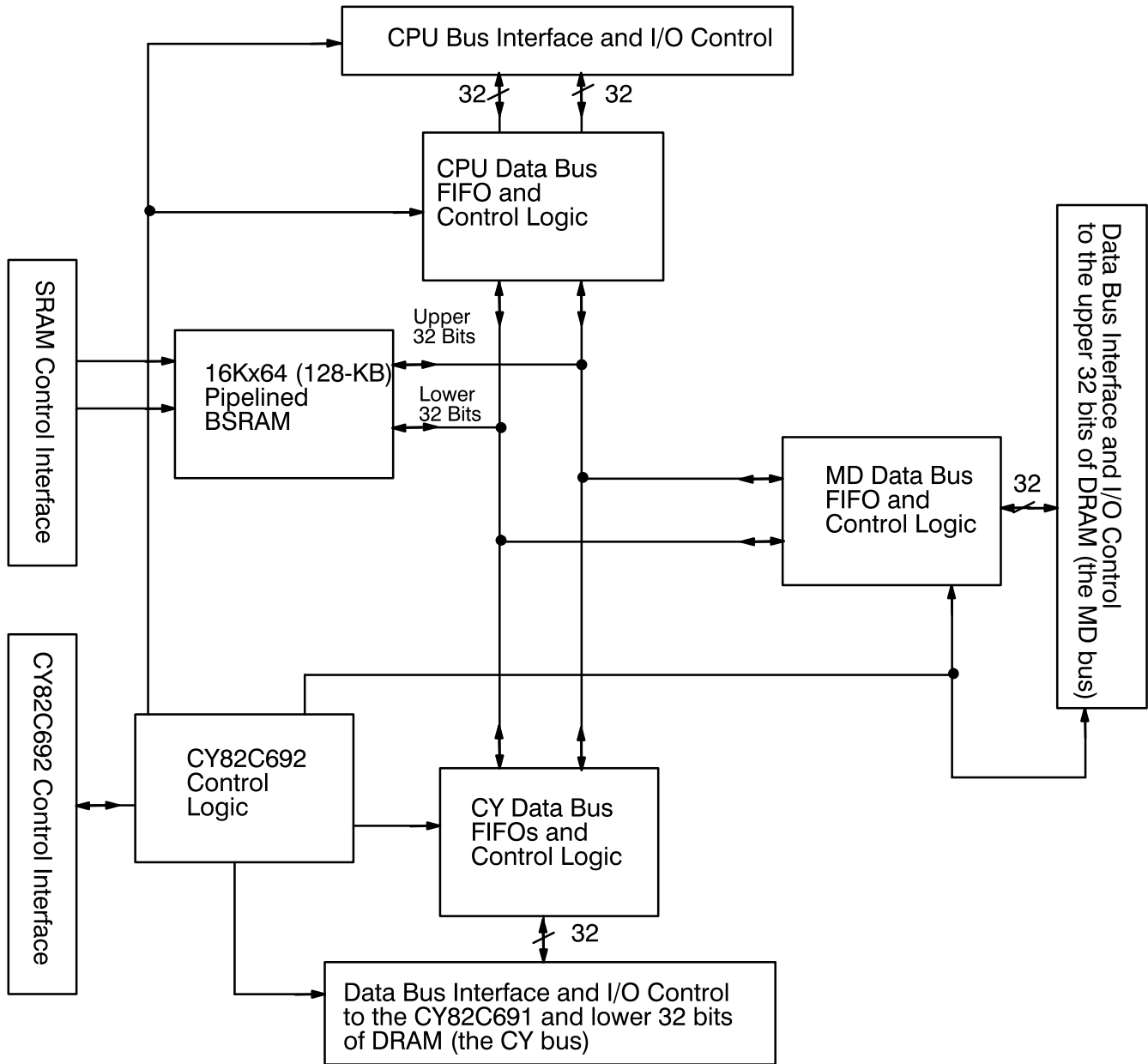
Features

- Supports all 3.3V Pentium™ -class processors (ICOMP 735/90, 815/100, etc.), AMD K5, and Cyrix M1 CPUs
- Directly interfaces with CY82C691 and CY82C693 to provide high-performance three-chip Pentium Chipset system
- Provides 64-bit data path between CPU, PCI, and DRAM memory
- 16K by 64 (128-KB) Integrated Pipelined BSRAM
- Direct-mapped or two-way set associative L2 cache mapping configurations
- Two-bit wraparound counter supporting Intel Burst or Linear burst sequence
- Supports 3-1-1 Level 2 cache operation up to 66 MHz bus speed
- Fast Clock-to-Data (T_{CO})=8.5 ns
- Synchronous self-timed write to L2 cache BSRAM
- Direct interface with the processor and the CY82C691 PCI/Cache/Memory Controller
- 3.3V I/O CPU bus operation
- On-Chip 8-Deep FIFOs support Post-Writing/Pre-Reading PCI data
- Supports Parity checking and generation
- Provides Data steering and Bus size conversion
- Packaged in a 208-pin PQFP

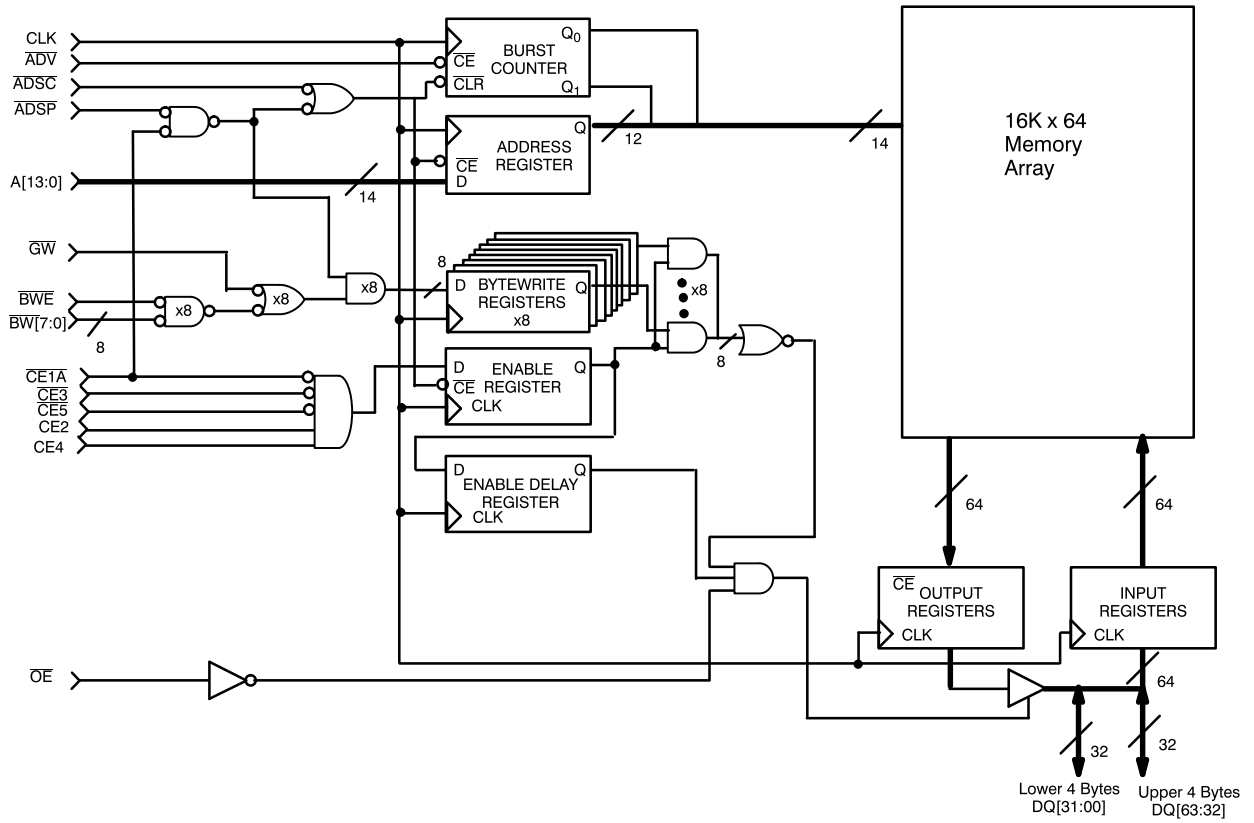


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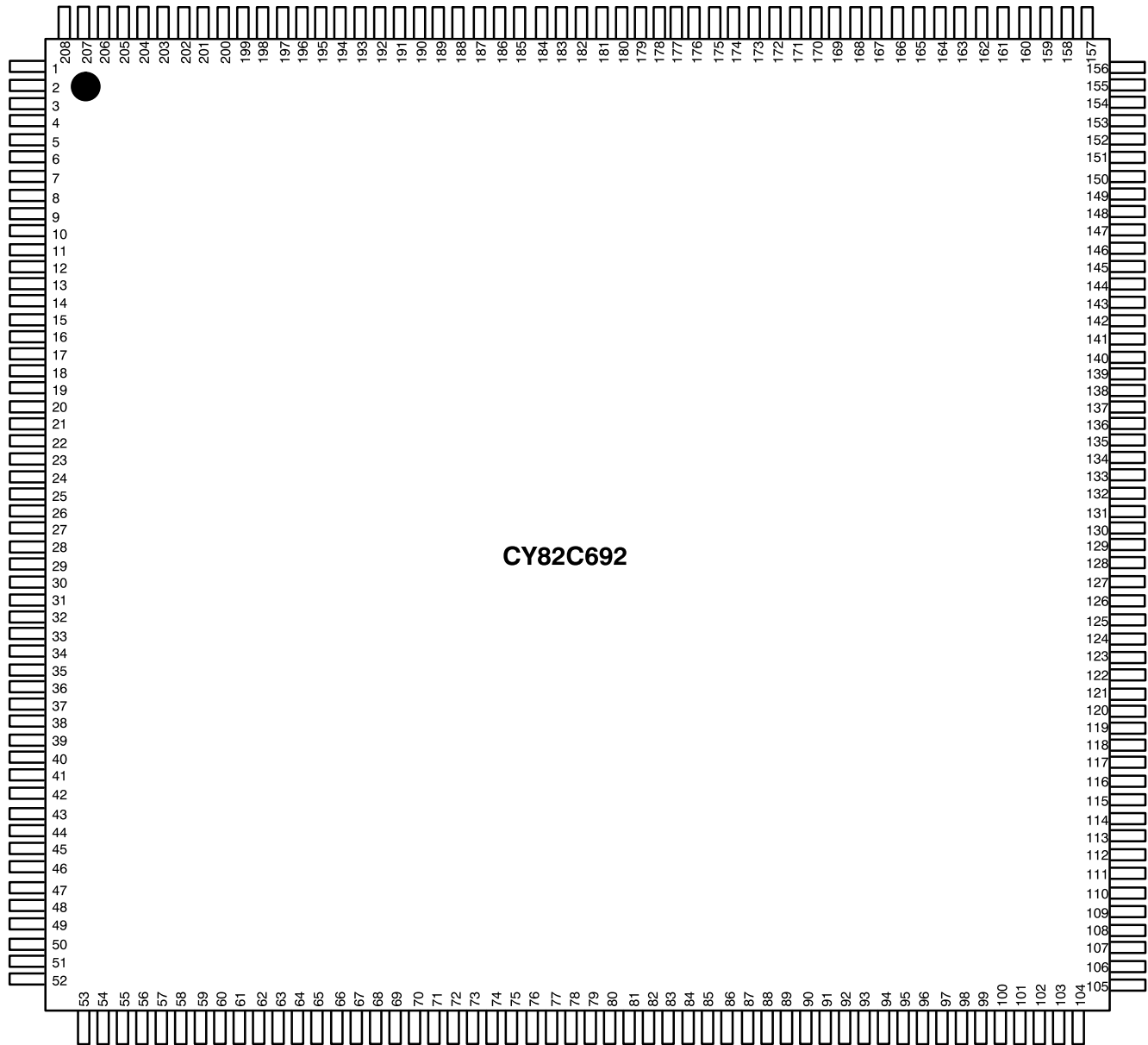
CY82C692 Block Diagram



SRAM Section Logic Block Diagram



82C692-98

Pin Configuration
**208-pin PQFP
Top View**


82C692-99

CY82C691 Pin Reference (In Numerical Order by Pin Number)

Pin No.	Pin Name	Pin No.	Pin Name	Pin No.	Pin Name	Pin No.	Pin Name	Pin No.	Pin Name
1	VSSQ	43	CY18	85	A5	127	DQ51	169	VDD
2	CY10	44	DQ28	86	MD63	128	DQ50	170	MD36
3	DQ0	45	CY19	87	A4	129	DQ49	171	VSS
4	CY11	46	DQ29	88	MD62	130	DQ48	172	MD35
5	DQ1	47	CY20	89	A3	131	DQ47	173	BW $\bar{2}$
6	CY12	48	DQ30	90	MD61	132	DQ46	174	MD34
7	DQ2	49	CY21	91	VDD	133	DQ45	175	BW $\bar{3}$
8	CY13	50	DQ31	92	MD60	134	DQ44	176	MD33
9	DQ3	51	CY22	93	VSS	135	DQ43	177	GW $\bar{}$
10	CY14	52	VDDQ	94	MD59	136	VDDQ	178	MD32
11	DQ4	53	VSSQ	95	A2	137	VSSQ	179	BW \bar{E}
12	CY15	54	CY23	96	MD58	138	DQ42	180	CNTL0
13	DQ5	55	CNTL4	97	A1	139	DQ41	181	CLK
14	MP1	56	MP2	98	MD57	140	DQ40	182	CNTL1
15	DQ6	57	CNTL5	99	A0	141	DQ39	183	OE
16	DQ7	58	CY24	100	RESET	142	DQ38	184	CNTL2
17	DQ8	59	NMI	101	MD56	143	MP5	185	BW $\bar{4}$
18	DQ9	60	CY25	102	MP6	144	DQ37	186	CNTL3
19	DQ10	61	CNTL6	103	MD55	145	MD47	187	BW $\bar{5}$
20	VDDQ	62	CY26	104	VDDQ	146	DQ36	188	CY0
21	VSSQ	63	A13	105	VSSQ	147	MD46	189	BW $\bar{6}$
22	DQ11	64	CY27	106	MD54	148	DQ35	190	CY1
23	DQ12	65	VDD	107	DQ63	149	MD45	191	BW $\bar{7}$
24	DQ13	66	CY28	108	MD53	150	DQ34	192	CY2
25	DQ14	67	VSS	109	DQ62	151	MD44	193	CE1A
26	DQ15	68	CY29	110	MD52	152	DQ33	194	CY3
27	DQ16	69	A12	111	DQ61	153	MD43	195	VDD
28	DQ17	70	CY30	112	MD51	154	DQ32	196	CY4
29	DQ18	71	A11	113	DQ60	155	MD42	197	VSS
30	DQ19	72	CY31	114	MD50	156	VDDQ	198	CY5
31	DQ20	73	A10	115	DQ59	157	VSSQ	199	CE2
32	VDDQ	74	MP3	116	MD49	158	MD41	200	CY6
33	VSSQ	75	A9	117	DQ58	159	ADV $\bar{}$	201	CE $\bar{3}$
34	DQ21	76	CNTL7	118	MD48	160	MD40	202	CY7
35	DQ22	77	A8	119	DQ57	161	ADSP $\bar{}$	203	CE4
36	DQ23	78	CNTL8	120	DQ56	162	MP4	204	MP0
37	DQ24	79	CNTL9	121	DQ55	163	ADSC $\bar{}$	205	CE $\bar{5}$
38	DQ25	80	CNTL10	122	DQ54	164	MD39	206	CY8
39	CY16	81	A7	123	DQ53	165	BW $\bar{0}$	207	CY9
40	DQ26	82	CNTL11	124	VDDQ	166	MD38	208	VDDQ
41	CY17	83	A6	125	VSSQ	167	BW $\bar{1}$		
42	DQ27	84	MP7	126	DQ52	168	MD37		

Introduction

System Overview

The CY82C691/692/693 hyperCache™ Chipset provides all the functions necessary to implement a 3.3V Pentium-class processor based system with the PCI (Peripheral Component Interconnect) bus and the ISA (Industry Standard Architecture) bus. The chipset consists of the CY82C691 System Controller, the CY82C692 Data Path/Cache chip, and the CY82C693 Peripheral Controller. System designers can exploit the advantages of the PCI bus while maintaining access to the large base of ISA cards in the marketplace.

The Cypress hyperCache Chipset offers system designers several key advantages. With only three chips, CY82C691/692/693, a complete system with a 128-KB, two-way set associative, synchronous pipelined L2 cache can be implemented. The cache size may be increased up to 1 MB with additional CY82C694 16Kx64 SRAMs or other synchronous or pipelined burst SRAMs. Six banks of page-mode or EDO DRAM further increase the system designer's options. The chipset also contains concurrent bus support, PCI enhanced IDE with CD-ROM support, integrated RTC, integrated peripheral control (Interrupts/DMA), and integrated keyboard controller. This chipset is flexible enough to provide the system designer with many cost/performance/function options to provide an optimum solution for a given design.

CY82C692 Introduction

The CY82C692 is a 64-bit data path unit between the DRAM and CPU with an integrated 128-KB (16Kx64) synchronous pipelined Burst SRAM (BSRAM). The CY82C692 serves two main functions: (1) Provides data steering to/from three different interfaces (CPU bus, the DRAM high or MD bus, and the DRAM low or CY bus), and (2) Provides 128 KB of Level 2 cache with an integrated synchronous pipelined BSRAM. With a clock-to-data valid time (T_{CO})=8.5 ns, 3-1-1 burst cycles are supported at bus frequencies up to 66 MHz.

The CY82C692 contains several sets of FIFOs that serve as Pre-Reading/Post-Writing buffers. These buffers are controlled by signals (Control[11:0]) coming from the CY82C691 System Controller. The Pre-Reading/Post-Writing feature enhances system performance by allowing concurrent transactions on the CPU, PCI, and DRAM buses.

The CY82C692 also contains data parity generation/checking logic for all transactions to/from DRAM memory.

The 3.3V CPU bus interface contains an 8-deep, 64-bit wide FIFO. This FIFO is logically broken into two 32-bit FIFOs in order to properly route data and accommodate for bus size conversions. All data coming from or going to the CPU data bus must pass through the CPU FIFO.

The DRAM interface is divided between the upper 32 bits and lower 32 bits of data. The upper 32 bits (and parity) are transferred on the MD bus. The MD bus is a dedicated connection between the CY82C692 and the upper 32 bits of DRAM memory. The lower 32 bits of data (and parity) are transferred on the CY bus. The CY bus also serves as the data path connecting the PCI bus (via the CY82C691) to the CPU.

The CY82C692 contains an integrated Level 2 cache configured as a 16Kx64 (128-KB) synchronous pipelined BSRAM. The BSRAM can be used as either a direct mapped or two-way set associative L2 cache. The BSRAM is controlled by dedicated control signals coming from the CY82C691 System Controller. The L2 cache can be expanded with additional CY82C694s

(Cypress's 16Kx64 pipelined BSRAM in a 128-pin TQFP) or additional discrete BSRAMs (synchronous or pipelined). Each bank must be comprised of the same type of BSRAM. L2 cache sizes of up to 1 MB are supported, with a maximum of 512 KB per bank.

Pre-Reading/Post-Writing

The CY82C692 supports Pre-Reading/Post-Writing operations through the use of on-chip 8-deep FIFOs that act as storage buffers. All Pre-Read and Post-Write operations are conducted to/from the on-chip FIFOs. Data is always stored in the FIFO closest to the target interface. By using these buffers in conjunction with on-chip control and routing logic, the CY82C692 is able to support concurrent transactions involving CPU, PCI, and DRAM memory transactions. All of the signals controlling the on-chip FIFOs are generated from the CY82C691 System Controller.

Parity Generation/Checking Logic

The CY82C692 contains the logic required for parity generation and checking. When enabled, the CY82C692 will check/generate even byte parity on the DRAM data lines. Generation will be done on all writes to DRAM memory and checking will be performed on all reads. If a parity error is encountered, the CY82C692 will assert an NMI directly to the CPU. Parity generation/checking can be disabled through register settings.

CPU Data Bus Interface

The CY82C692 interfaces to the CPU data bus through a 3.3V 64-bit interface. On-chip logic divides this interface into two 32-bit words in order to accommodate bus size conversions and concurrent transactions. Each 32-bit word passes through a 8-deep FIFO and three-state buffers.

DRAM Interface

The CY82C692 connects to DRAM memory through two separate 32-bit data interfaces, the CY and MD buses. The CY bus connects the lower 32-bits of data (and parity) to both the DRAM memory and the CY82C691 System Controller. The CY bus interface contains two 32-bit-wide, 8-deep FIFOs in order to store Pre-Read/Post-Write data. The FIFO is controlled by Control[11:0] from the CY82C691 System Controller. Additionally, all CPU-to-PCI transactions are routed through the CY bus to the CY82C691 System Controller.

The upper 32 bits of DRAM data are transferred on the MD bus. The MD bus is a dedicated interface that connects the CY82C692 with the upper 32 bits of DRAM data (and parity). The MD bus interface contains two 32-bit-wide 8-deep FIFOs that are used to store Pre-Read/Post-Write data destined for upper memory. FIFO control is conducted through Control[11:0].

Integrated Level 2 Cache

The CY82C692 contains an integrated Level 2 cache configured as a 16Kx64 (128-KB) synchronous pipelined Burst SRAM (BSRAM). The BSRAM operates as a separate device, independent from the other functional blocks of the CY82C692. The BSRAM can be used as either a direct mapped or two-way set associative 128-KB Level 2 cache. Level 2 cache expansion can be accomplished with either additional CY82C694s (up to a total of eight for a 1-MB L2 cache), or additional dedicated BSRAMs (synchronous or pipelined). Each bank must be comprised of the same type of BSRAM. L2 cache sizes of up to 1MB are supported. A maximum of two banks of L2 cache is

allowed, with a maximum of 512 KB per bank. If desired, the BSRAM inside the CY82C692 can also be disabled.

All synchronous inputs to the BSRAM pass through registers controlled by a positive edge triggered single clock (CLK). The synchronous inputs include all addresses, data inputs, write inputs ($\overline{BW}[7:0]$, \overline{GW} , \overline{BWE}), \overline{ADSP} , \overline{ADSC} , \overline{ADV} , and chip enables ($\overline{CE1A}$, $\overline{CE2}$, $\overline{CE3}$, $\overline{CE4}$, $\overline{CE5}$).

All data outputs pass through output registers controlled by the rising edge of the clock. Maximum access delay from the clock rise (T_{CO}) is 8.5 ns. A two-bit on-chip wraparound burst counter captures the first address in a burst sequence and automatically increments the address for the rest of the burst access.

The CY82C692 supports secondary cache in systems utilizing either a linear or interleaved burst sequence. The interleaved burst order supports Intel and AMD processors. The linear burst sequence is suited for processors such as the Cyrix M1. The burst order is user selectable, and is determined by writing to a specified register during power-up. Accesses can be initiated with either the processor address strobe (\overline{ADSP}) or the controller address strobe (\overline{ADSC}). Address advancement through the burst sequence is controlled by the \overline{ADV} input.

Byte write operations are qualified with the Byte Write Enable (\overline{BWE}) and Byte Write Select ($\overline{BW0-7}$) inputs. A Global Write Enable (\overline{GW}) overrides all byte write inputs and writes data to all eight bytes. All writes are simplified with on-chip synchronous self-timed write circuitry.

Five synchronous chip selects ($\overline{CS1A}$, $\overline{CS3}$, $\overline{CS5}$, $\overline{CS2}$, $\overline{CS4}$) and an asynchronous output enable (\overline{OE}) provide for easy bank selection and output three-state control.

Single Read Accesses

This access is initiated when the following conditions are satisfied at clock rise: (1) \overline{ADSP} or \overline{ADSC} is asserted LOW, (2) $\overline{CS1A}$, $\overline{CS3}$, $\overline{CS5}$, $\overline{CS4}$, and $\overline{CS2}$ are all asserted active, and (3) the write signals ($\overline{BW0-7}$, \overline{GW} , \overline{BWE}) are all deasserted HIGH. The address presented to the address inputs ($A0-A13$) is stored into the address advancement logic and the Address Register while being presented to the memory core. The corresponding data is allowed to propagate to the input of the Output Registers of the SRAM section. At the rising edge of the next clock the data is allowed to propagate through the output register, through the CPU bus FIFO, and is driven onto the CPU data bus on $D[63:00]$. The requested data will be available on the CPU bus 8.5 ns after the clock rise. When the asynchronous Output Enable (\overline{OE}) is asserted LOW, the data outputs from the SRAM block are controlled by the Enable and Enable Delay Registers. During the first cycle of an initial read operation the outputs on the CPU bus remain in a three-state condition, regardless of the state of Output Enable (\overline{OE}). This feature is required in order to support pipelining without creating contention on the data bus when multiple banks of cache are used. Consecutive single read cycles are supported.

Single Write Accesses Initiated by \overline{ADSP}

\overline{ADSP} -triggered accesses are initiated when both of the following conditions are satisfied at clock rise: (1) \overline{ADSP} is asserted LOW, and (2) $\overline{CS1A}$, $\overline{CS3}$, $\overline{CS5}$, $\overline{CS4}$, and $\overline{CS2}$ are all asserted active. The address presented to $A0-A13$ is loaded into the address register and the address advancement logic while being delivered to the RAM core. The write signals ($\overline{BW0-7}$, \overline{GW} , \overline{BWE}) and \overline{ADV} inputs are ignored during this first cycle.

\overline{ADSP} triggered write accesses require two clock cycles to complete. If the write inputs ($\overline{BW}[7:0]$, \overline{GW} , \overline{BWE}) are asserted LOW on the second clock rise, the data presented to the $D0-D63$ inputs is written into the corresponding address location in the RAM core. The CY82C692 provides byte write capability. Asserting the appropriate Byte Write (\overline{GW} , \overline{BWE} , $\overline{BW0-7}$) input will selectively write to only the desired bytes. Bytes not selected during a byte write operation will remain unaltered. A Synchronous self-timed write mechanism has also been provided to simplify the write operations.

Since the CY82C692 is a common I/O device, the Output Enable (\overline{OE}) must be deasserted HIGH before presenting data to the $D0-D63$ inputs. Doing so will three-state the output drivers. As a safety precaution, $D0-D63$ are automatically three-stated whenever a write cycle is detected, regardless of the state of \overline{OE} .

Single Write Accesses Initiated by \overline{ADSC}

\overline{ADSC} write accesses in Pipelined mode are initiated when the following conditions are satisfied: (1) \overline{ADSC} is asserted LOW, (2) \overline{ADSP} is deasserted HIGH, (3) $\overline{CS1A}$, $\overline{CS5}$, $\overline{CS3}$, $\overline{CS4}$, and $\overline{CS2}$ are all asserted active, and (4) the appropriate write inputs (\overline{GW} , \overline{BWE} , $\overline{BW0-7}$) are asserted active to conduct a write to the desired byte(s). \overline{ADSC} triggered write accesses require a single clock cycle to complete. The address presented to $A0-A13$ is loaded into the address register and the address advancement logic while being delivered to the RAM core. The \overline{ADV} input is ignored during this cycle. The data presented to the $D0-D63$ is written into the corresponding address location in the RAM core. If a byte write is conducted, only the selected bytes are written. Bytes not selected during a byte write operation will remain unaltered. A Synchronous self-timed write mechanism has also been provided to simplify the write operations.

Since the CY82C692 is a common I/O device, the Output Enable (\overline{OE}) must be deasserted HIGH before presenting data to the $D0-D63$ inputs. Doing so will three-state the output drivers. As a safety precaution, $D0-D63$ are automatically three-stated whenever a write cycle is detected, regardless of the state of \overline{OE} .

Burst Sequences

The CY82C692 provides a two-bit wraparound counter, fed by $A0$ and $A1$, that implement either an interleaved or linear burst sequence. The interleaved burst sequence is designed specifically to support Intel Pentium applications. The linear burst sequence is designed to support processors that follow a linear burst sequence, such as the Cyrix M1. The burst order is determined during boot-up by writing to a specific configuration register.

Asserting \overline{ADV} LOW at clock rise will automatically increment the burst counter to the next address in the burst sequence. Both read and write burst operations are supported.

Intel Burst Sequence

First Address	Second Address	Third Address	Fourth Address
Ax+1, Ax	Ax+1, Ax	Ax+1, Ax	Ax+1, Ax
00	01	10	11
01	00	11	10
10	11	00	01
11	10	01	00

Linear Burst Sequence

First Address	Second Address	Third Address	Fourth Address
Ax+1, Ax	Ax+1, Ax	Ax+1, Ax	Ax+1, Ax
00	01	10	11
01	10	11	00
10	11	00	01
11	00	01	10

Cycle Descriptions

Next Cycle	Add. Used	CS2	CS4	CS3	CS5	CS1A	ADSP	ADSC	ADV	OE	DQ	Writes
Unselected	none	X	X	X	X	1	X	0	X	X	Hi-Z	X
Unselected	none	0	X	X	X	0	0	X	X	X	Hi-Z	X
Unselected	none	X	0	X	X	0	0	X	X	X	Hi-Z	X
Unselected	none	X	X	1	X	0	0	X	X	X	Hi-Z	X
Unselected	none	X	X	X	1	0	0	X	X	X	Hi-Z	X
Unselected	none	0	X	X	X	0	1	0	X	X	Hi-Z	X
Unselected	none	X	0	X	X	0	1	0	X	X	Hi-Z	X
Unselected	none	X	X	1	X	0	1	0	X	X	Hi-Z	X
Unselected	none	X	X	X	1	0	1	0	X	X	Hi-Z	X
Begin Read	External	1	1	0	0	0	0	X	X	X	Hi-Z	X
Begin Read	External	1	1	0	0	0	1	0	X	X	Hi-Z	Read
Continue Read	Next	X	X	X	X	X	1	1	0	1	Hi-Z	Read
Continue Read	Next	X	X	X	X	X	1	1	0	0	DQ	Read
Continue Read	Next	X	X	X	X	1	X	1	0	1	Hi-Z	Read
Continue Read	Next	X	X	X	X	1	X	1	0	0	DQ	Read
Suspend Read	Current	X	X	X	X	X	1	1	1	1	Hi-Z	Read
Suspend Read	Current	X	X	X	X	X	1	1	1	0	DQ	Read
Suspend Read	Current	X	X	X	X	1	X	1	1	1	Hi-Z	Read
Suspend Read	Current	X	X	X	X	1	X	1	1	0	DQ	Read
Begin Write	Current	X	X	X	X	X	1	1	1	X	Hi-Z	Write ^[1]
Begin Write	Current	X	X	X	X	1	X	1	1	X	Hi-Z	Write ^[1]
Begin Write	External	1	1	0	0	0	1	0	X	X	Hi-Z	Write ^[1]
Continue Write	Next	X	X	X	X	X	1	1	0	X	Hi-Z	Write ^[1]
Continue Write	Next	X	X	X	X	1	X	1	0	X	Hi-Z	Write ^[1]
Suspend Write	Current	X	X	X	X	X	1	1	1	X	Hi-Z	Write ^[1]
Suspend Write	Current	X	X	X	X	1	X	1	1	X	Hi-Z	Write ^[1]

X=Don't Care, 1=Logic HIGH, 0=Logic LOW.

Note:

- Writes defined by \overline{BWE} , $\overline{BW}[7:0]$, and \overline{GW} , see Write Cycle Description table.

Write Cycle Descriptions

Function ^[2]	\overline{GW}	\overline{BWE}	$\overline{BW7}$	$\overline{BW6}$	$\overline{BW5}$	$\overline{BW4}$	$\overline{BW3}$	$\overline{BW2}$	$\overline{BW1}$	$\overline{BW0}$
Read	1	1	X	X	X	X	X	X	X	X
Read	1	0	1	1	1	1	1	1	1	1
Write All Byte	0	X	X	X	X	X	X	X	X	X
Write Byte 0 – DQ[7:0]	1	0	1	1	1	1	1	1	1	0
Write Byte 1 – DQ[15:8]	1	0	1	1	1	1	1	1	0	1
Write Byte 2 – DQ[23:16]	1	0	1	1	1	1	1	0	1	1
Write Byte 3 – DQ[31:24]	1	0	1	1	1	1	0	1	1	1
Write Byte 4 – DQ[39:32]	1	0	1	1	1	0	1	1	1	1
Write Byte 5 – DQ[47:40]	1	0	1	1	0	1	1	1	1	1
Write Byte 6 – DQ[55:48]	1	0	1	0	1	1	1	1	1	1
Write Byte 7 – DQ[63:56]	1	0	0	1	1	1	1	1	1	1
Write Byte 1, 0	1	0	1	1	1	1	1	1	0	0
Write Byte 2, 1	1	0	1	1	1	1	1	0	0	1
Write Byte 2, 0	1	0	1	1	1	1	1	0	1	0
Write Byte 2, 1, 0	1	0	1	1	1	1	1	0	0	0
Write Byte 3, 0	1	0	1	1	1	1	0	1	1	0
Write Byte 3, 1	1	0	1	1	1	1	0	1	0	1
Write Byte 3, 1, 0	1	0	1	1	1	1	0	1	0	0
Write Byte 3, 2	1	0	1	1	1	1	0	0	1	1
Write Byte 3, 2, 0	1	0	1	1	1	1	0	0	1	0
Write Byte 3, 2	1	0	1	1	1	1	0	0	1	1

The remainder follows the same pattern as above.

X=Don't Care, 1=Logic HIGH, 0=Logic LOW.

Notes:

- The SRAM always starts a Read cycle when $\overline{ADS\overline{P}}$ is asserted, regardless of the state of \overline{GW} , \overline{BWE} , $\overline{BW}[7:0]$.

Pin Descriptions

Name	I/O	Pin Number	Description
RESET	I	100	This is the RESET input signal from the CY82C693. It puts the CY82C692 into a known state and invalidates all write-buffer entries.
CPUCLK	I	181	The CPU clock input. This runs synchronous to the CPU's external clock.
D[63:00]	I/O	107, 109, 111, 113, 115, 117, 119–123, 126–135, 138–142, 144, 146, 148, 150, 152, 154, 50, 48, 46, 44, 42, 40, 38–34, 31–22, 19-15, 13, 11, 9, 7, 5, 3	The 64-bit CPU data bus interface. These are 3.3V signals.
CY[31:00]	I/O	72, 70, 68, 66, 64, 62, 60, 58, 54, 51, 49, 47, 45, 43, 41, 39, 12, 10, 8, 6, 4, 2, 207, 206, 202, 200, 198, 196, 194, 192, 190, 188	The CY bus interfaces to the lower 32 DRAM data bits. It also is the data path to pass data to/from the CY82C691 for routing to the PCI bus.
MD[63:31]	I/O	86, 88, 90, 92, 94, 96, 98, 101, 103, 106, 108, 110, 112, 114, 116, 118, 145, 147, 149, 151, 153, 155, 158, 160, 164, 166, 168, 170, 172, 174, 176, 178	The MD bus interfaces to the upper 32 DRAM data bits.
MP[7:0]	I/O	84, 102, 143, 162, 74, 56, 14, 204	Memory parity bits. The CY82C692 generates/checks even byte parity on the DRAM data lines.
NMI	O	59	Non-maskable interrupt line to the CPU. Used to inform the CPU that a parity error has been detected.
A[13:0]	I	63, 69, 71, 73, 75, 77, 81, 83, 85, 87, 89, 95, 97, 99	Address inputs to the cache BSRAM, sampled on the rising edge of the clock.
\overline{GW}	I	177	Global Write Enable input. Used in to conduct global writes. When asserted, \overline{GW} overrides all byte writes, and a global write occurs. When used with the CY82C691 and CY82C693, this pin should be tied HIGH through a 1K Ω resistor.
\overline{BWE}	I	179	Byte Write Enable input. Used in conjunction with $\overline{BW}[7:0]$ to conduct byte write operations. $\overline{BW}[7:0]$ are qualified with \overline{BWE} . When asserted, \overline{GW} overrides all byte writes, and a global write occurs. When used with the CY82C691 and CY82C693, this pin should be tied LOW through a 1K Ω resistor.
$\overline{BW}[7:0]$	I	191, 189, 187, 185, 175, 173, 167, 165	Byte write inputs to the cache BSRAM, synchronous, sampled on the rising edge of the clock.
$\overline{CE1A}$	I	193	Chip enable and \overline{ADSP} mask.

Pin Descriptions (continued)

Name	I/O	Pin Number	Description
CE2, $\overline{\text{CE3}}$, CE4, CE5	I	199, 201, 203, 205	Expansion decode inputs for L2 cache expansion. Used to establish and decode the expansion position of each CY82C692.
$\overline{\text{OE}}$	I	183	Asynchronous Output Enable. Active LOW, used in conjunction with Control[11:00] to control the three-state buffers onto the CPU bus.
$\overline{\text{ADV}}$	I	159	Advance input signal to the BSRAM section only, active LOW, sampled on the rising edge of the clock. When detected active it will cause the on-chip burst counter to increment to the next address in the burst sequence. This signal is ignored if $\overline{\text{ADSP}}$ or $\overline{\text{ADSC}}$ is asserted.
$\overline{\text{ADSC}}$	I	163	Address input strobe from the controller, active LOW, sampled on the rising edge of the clock. When asserted, the address inputs are captured in the address register. A0 and A1 are also loaded into the two-bit burst counter. $\overline{\text{ADSC}}$ is ignored when asserted with $\overline{\text{ADSP}}$.
$\overline{\text{ADSP}}$	I	161	Address input strobe from the processor, active LOW, sampled on the rising edge of the clock. When asserted, the address inputs are captured in the address register. A0 and A1 are also loaded into the two-bit burst counter.
CONTROL [11:00]	I	82, 80–78, 76, 61, 57, 55, 186, 184, 182, 180	Control inputs. These are the inter-chip communication signals between the CY82C691 and CY82C692. These signals are used to control the FIFOs, logic, three-stating, and data steering inside the CY82C692.
V _{DDQ}	Supply	20, 32, 52, 104, 124, 136, 156, 208	3.3 or 5V power supply for the I/Os of the to the CY82C692.
V _{DD}	Supply	65, 91, 169, 195	5V power supply to the core of the CY82C692.
V _{DDQ}	GND	1, 21, 33, 53, 105, 125, 137, 157	Ground for the I/Os of the CY82C692.
V _{SS}	GND	67, 93, 171, 197	Ground for the core of the CY82C692.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature -65°C to +150°C

Ambient Temperature with

Power Applied -55°C to +125°C

Supply Voltage on V_{DD} Relative to GND -0.5V to +7.0V

DC Voltage Applied to Outputs in High Z State^[3] -0.5V to V_{DD} + 0.5V

DC Input Voltage^[2] -0.5V to V_{DD} + 0.5V

Current into Outputs (LOW) 20 mA

Static Discharge Voltage >2001V (per MIL-STD-883, Method 3015)

Latch-Up Current >200 mA

Operating Range

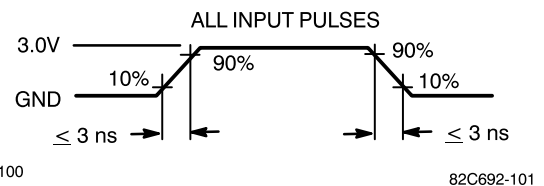
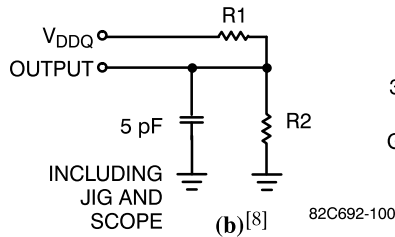
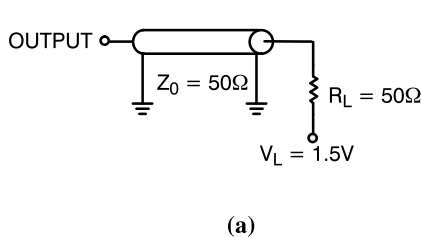
Range	Ambient Temperature ^[4]	V _{DD}	V _{DDQ}
Com'l	0°C to +70°C	5V ± 5%	3.0V to V _{DD}

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions	Min.	Max.	Unit
V _{OH}	Output HIGH Voltage	V _{DD} = Min., I _{OH} = -5.0 mA	2.4	V _{DDQ}	V
V _{OL}	Output LOW Voltage	V _{DD} = Min., I _{OL} = 5.0 mA		0.4	V
V _{IH}	Input HIGH Voltage		2.0	V _{DD} + 0.3V	V
V _{IL}	Input LOW Voltage ^[2]		-0.3	0.8	V
I _X	Input Load Current	GND ≤ V _I ≤ V _{DD}	-1	1	μA
I _{OZ}	Output Leakage Current	GND ≤ V _I ≤ V _{DD} , Output Disabled	-5	5	μA
I _{OS}	Output Short Circuit Current ^[5]	V _{DD} = Max., V _{OUT} = GND		-300	mA
I _{CC}	V _{DD} Operating Supply Current	V _{DD} = Max., I _{out} = 0mA, f = f _{MAX} = 1/t _{CYC}	Com'l	350	mA
I _{SB1}	Automatic CS Power-Down Current – TTL Inputs	Max. V _{DD} , $\overline{CS} \geq V_{IH}$, V _{IN} ≥ V _{IH} or V _{IN} ≤ V _{IL} , f = f _{MAX}	Com'l	100	mA
I _{SB2}	Automatic CS Power-Down Current – CMOS Inputs	Max. V _{DD} , $\overline{CS} \geq V_{DD} - 0.3V$, V _{IN} ≥ V _{DD} - 0.3V or V _{IN} ≤ 0.3V, f = 0 ^[6]	Com'l	45	mA

Capacitance^[7]

Parameter	Description	Test Conditions	Max.	Unit
C _{IN} : Addresses	Input Capacitance	T _A = 25°C, f = 1 MHz, V _{DD} = 5.0V	4.5	pF
C _{IN} : Other Inputs			5	pF
C _{OUT}	Output Capacitance		8	pF

AC Test Loads and Waveforms

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
8	CY82C692-XXX	TBD	208-Lead Plastic Quad Flat Pack	Commercial
10	CY82C692-XXX	TBD	228-Lead Plastic Quad Flat Pack	Commercial

Notes:

- Minimum voltage equals -2.0V for pulse durations of less than 20 ns.
- T_A is the "instant on" case temperature.
- Not more than one output should be shorted at one time. Duration of the short circuit should not exceed 30 seconds.
- Inputs are disabled, clock is allowed to run at speed.
- Tested initially and after any design or process changes that may affect these parameters.
- Resistor values for V_{DDQ} = 5V are: R₁ = 1179Ω and R₂ = 868Ω. Resistor values for V_{DDQ} = 3.3V are R₁ = 317Ω and R₂ = 348Ω.

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